

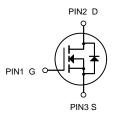
## **Description**

The IRLML6244PbF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ ,low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **SOT-23**

## **General Features**

 $V_{DS}$  = 20V, $I_D$  = 7A  $R_{DS(ON)}$  < 17m $\Omega$  @ VGS=4.5V  $R_{DS(ON)}$  < 25m $\Omega$  @ VGS=2.5V



#### N-Channel MOSFET

# **Application**

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
IRLML6244PbF	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>G</sub> S	Gate-Source Voltage	±12	V
<b>I</b> D	Drain Current-Continuous	7	Α
Ірм	Drain Current-Pulsed (Note 1)	32	А
P <sub>D</sub>	Maximum Power Dissipation	2	W
Тյ,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\!\mathbb{C}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	120	°C/W

# Electrical Characteristics (TJ=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20	-	_	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	-	-	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.75	1.2	V
	Static Drain-Source on-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =7A	-	15	17	mΩ
$R_{DS(on)}$	note2	V <sub>GS</sub> =2.5V, I <sub>D</sub> =5A	-	19	25	
C <sub>iss</sub>	Input Capacitance	10 10 1	-	700	_	pF
Coss	Output Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHz	-	132	-	pF
Crss	Reverse Transfer Capacitance	- 1-1.0WI12	-	114	-	pF
Qg	Total Gate Charge	\/ -40\/ I -40	-	15	-	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =10V, I <sub>D</sub> =4A, V <sub>GS</sub> =4.5V	-	2	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	5.2	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	1/ 40\/	-	9	_	ns
t <sub>r</sub>	Turn-on Rise Time	$V_{DS}$ =10V, $I_{D}$ =4A, $R_{GEN}$ =3 $\Omega$ ,	-	25	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	V <sub>GS</sub> =4.5V	-	37	-	ns
t <sub>f</sub>	Turn-off Fall Time	7 63 7.00	-	14	-	ns
, 1	Maximum Continuous Drain to Source Diode Forward				7.5	Α
I <sub>S</sub> Current			-	_	7.5	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	Α
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



# **Typical Performance Characteristics**

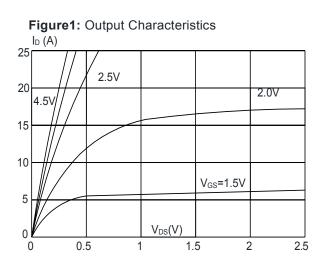


Figure 2: Typical Transfer Characteristics

25

20

15

10

5

125°C

25°C

0

0

0

0

0

0

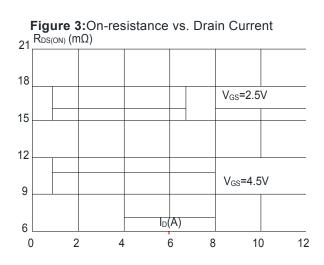
0

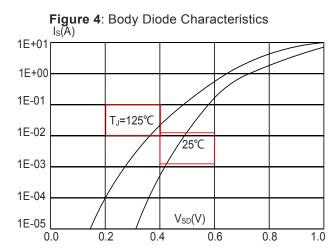
1.5

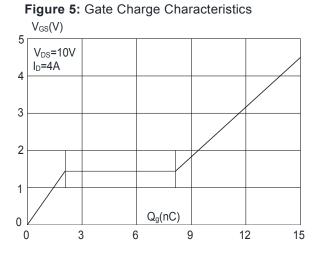
2.0

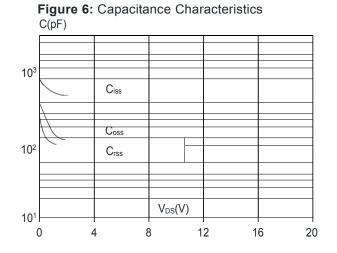
2.5

3.0











**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

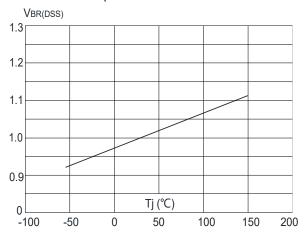
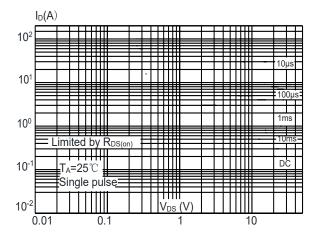
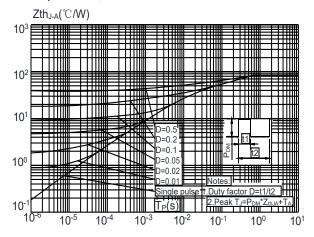


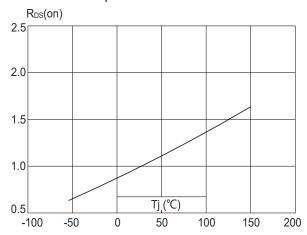
Figure 9: Maximum Safe Operating Area



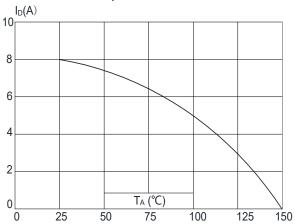
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



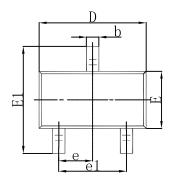
**Figure 8:** Normalized on Resistance vs. Junction Temperature

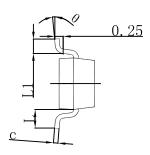


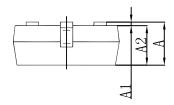
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



# **SOT-23 Package Outline Dimensions**

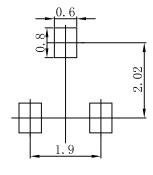






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



#### Note

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
  3.The pad layout is for reference purposes only.



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